

TSMC97-542/TSMC98-021

PLEASE AMEND THE SPECIFICATIONS AS FOLLOWS:

page 4, line 4, replace "4,702,492" with --4,702,792--.

PLEASE AMEND THE CLAIMS AS FOLLOWS:

1 (AMENDED) A method of forming and planarizing copper layer,

comprising the steps of:

providing a substrate;

forming dual damascene trenches in said substrate;

depositing a barrier metal layer on said substrate and in said dual

damascene trenches;

depositing a seed layer on top of said barrier metal layer;

electroplating a copper layer on top of said seed layer by means of
forward current electroplating;

forming a reverse tone photoresist mask;

[removing] etching away that part of said copper layer and said barrier
metal layer not covered by said reverse tone photoresist mask by means of
reverse current electroplating;

stripping of said photoresist;

TSMC97-542/TSMC98-021

*B¹
cont*

planarizing by chemical mechanical polishing (CMP) said now exposed
copper layer and barrier metal layer; and
sealing said copper layer with a cap layer.

/

PLEASE CANCEL CLAIM 3.